Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (withdrawn): A method for producing a light emitting diode, which has a plated substrate with a mirror, comprising steps of:

a) providing a substrate with an LED epitaxial structure including a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer sequentially formed on said substrate;

b) etching a part of said LED epitaxial structure to expose said second cladding layer;

c) forming a first electrode and a second electrode respectively on said metal contact layer and said exposed second cladding layer, and heating both said electrodes by rapid thermal annealing;

d) bonding a temporary substrate to said LED epitaxial structure and said first electrode;

e) removing said substrate provided in step a);

f) forming a mirror beneath said LED epitaxial structure;

g) plating a permanent substrate beneath said mirror; and

h) removing said temporary substrate.

Claim 2 (withdrawn): The method as claimed in claim 1, wherein said substrate provided in step a) is a GaAs substrate, a sapphire substrate or an InP substrate.

Claim 3 (withdrawn): The method as claimed in claim 1, wherein said LED epitaxial structure is made from a material selected from the group

consisting of $Ga_xAl_yIn_{1-x-y}N$, $(Al_xGa_{1-x})_yIn_{1-y}P$, $In_xGa_{1-x}As$, ZnS_xSe_{1-x}; wherein $0 \leq x \leq 1$, $0 \leq y \leq 1$.

Claim 4 (withdrawn): The method as claimed in claim 1, wherein said metal contact layer is partially etched to retain a portion beneath said first electrode.

Claim 5 (withdrawn): The method as claimed in claim 1 further depositing a transparent conductive film between said first electrode and said metal contact layer.

Claim 6 (withdrawn): The method as claimed in claim 1, wherein said temporary substrate is a glass substrate.

Claim 7 (withdrawn): The method as claimed in claim 1, wherein said temporary substrate is bonded to said LED epitaxial structure with epoxy or wax.

Claim 8 (withdrawn): The method as claimed in claim 1, wherein said mirror is a metal capable of forming high bandgap with said LED epitaxial structure.

Claim 9 (withdrawn): The method as claimed in claim 8, wherein said mirror is made from a material selected from the group consisting of Ag, Pt, Pd, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni, In, Sn, Al, Zn, Ge and Ni, or mixtures thereof.

Claim 10 (withdrawn): The method as claimed in claim 1, wherein said mirror is made from a composite of a metal with a low refractivity and an insulating layer with a high refractivity, and said insulating layer is adjacent to said LED epitaxial structure.

Claim 11 (withdrawn): The method as claimed in claim 10, wherein said composite is selected from the group consisting of Al/Al_2O_3, Al/SiO_2, Al/MgF_2, Pt/Al_2O_3, Pt/SiO_2, Pt/MgF_2, Al/Al_2O_3, Al/SiO_2, Al/MgF_2, Au/Al_2O_3, Au/SiO_2, Au/MgF_2, Ag/Al_2O_3, Ag/SiO_2, Ag/MgF_2.

Claim 12 (withdrawn): The method as claimed in claim 1, wherein said permanent substrate is plated beneath said mirror other than predetermined saw streets.

Claim 13 (currently amended): A light emitting diode having a plated substrate with a mirror, comprising:

an LED epitaxial structure sequentially comprising a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer, wherein said second cladding layer is partially exposed , ~~wherein said active layer is made from a material selected from the group consisting of $(Al_xGa_{1-x})_yIn_{1-y}P$, $Ga_xAl_yIn_{1-x-y}N$, $In_xGa_{1-x}As$, and ZnS_xSe_{1-x}, $0\leq x\leq 1$, $0\leq y\leq 1$;~~

a first electrode formed on said metal contact layer;

a second electrode formed on said exposed second cladding layer;

a mirror formed beneath said LED epitaxial structure; and

a ~~permanent metal~~ copper substrate plated beneath said mirror and retaining sawing streets without plating the substrate thereon;

wherein said mirror is made from a composite~~, a metal or an alloy~~ of a metal layer with low refractivity and an insulating layer with high refractivity, adjacent to the LED epitaxial structure, selected from the group consisting of:

Al/MgF_2, Pt/Al_2O_3, Pt/SiO_2, Pt/MgF_2, Au/SiO_2, Au/MgF_2, Ag/MgF_2;

~~Ag, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni and Zn, or mixtures thereof when said active layer is made from $(Al_xGa_{1-x})_yIn_{1-y}P$;~~

~~Ag, Pt, Pd, Al, and Ni, or mixtures thereof when said active layer is made from $Ga_xAl_yIn_{1-x-y}N$, $0\leq x\leq 1$, $0\leq y\leq 1$;~~

~~Ag, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni and Zn, or mixtures thereof when said active layer is made from $In_xGa_{1-x}As$, $0\leq x\leq 1$, $0\leq y\leq 1$; or~~

~~Ag, Pt, Pd, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni, Al and Ni, or mixtures thereof when said active layer is made from ZnS_xSe_{1-x}, $0\leq x\leq 1$, $0\leq y\leq 1$~~.

Claim 14 (canceled)

Claim 15 (original): The light emitting diode as claimed in claim 13 further comprising a transparent conductive film between said first electrode and said metal contact layer.

Claims 16-25 (canceled)

Claim 26 (new): The light emitting diode as claimed in claim 13, wherein the copper substrate is an electroless copper substrate with 30μm thick.

Claim 27 (new): The light emitting diode as claimed in claim 13 further comprising a film of Pd, coated beneath the metal layer of the mirror, to accelerate the reaction of electroless copper substrate.

Claim 28 (new): The light emitting diode as claimed in claim 13, wherein said metal contact layer remains only the portion beneath the first electrode.

Claim 29 (new): A light emitting diode having a plated substrate with a mirror, comprising:

an LED epitaxial structure sequentially comprising a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer, wherein said second cladding layer is partially exposed;

a first electrode formed on said metal contact layer;

a second electrode formed on said exposed second cladding layer;

a mirror formed beneath said LED epitaxial structure; and

a copper substrate plated beneath said mirror and retaining sawing streets without plating the substrate thereon;

wherein said metal contact layer remains only the portion beneath the first electrode;

wherein said mirror is made from a composite of a metal layer with low refractivity and an insulating layer with high refractivity, adjacent to said LED epitaxial structure, selected from the group consisting of: Al/MgF_2, Pt/Al_2O_3, Pt/SiO_2, Pt/MgF_2, Au/SiO_2, Au/MgF_2, Ag/MgF_2.

Claim 30 (new): The light emitting diode as claimed in claim 29, wherein said

copper substrate is formed by using electroless plating.

Claim 31 (new): The light emitting diode as claimed in claim 29, wherein said copper substrate is about 30μm thick.

Claim 32 (new): The light emitting diode as claimed in claim 29 further comprising a transparent conductive film between said first electrode and said metal contact layer.

Claim 33 (new): The light emitting diode as claimed in claim 30 further comprising a film of Pd, coated beneath the metal layer of the mirror, to accelerate the reaction of electroless copper substrate.

Claim 34 (new): A light emitting diode having a plated substrate with a mirror, comprising:

an LED epitaxial structure sequentially comprising a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer, wherein said second cladding layer is partially exposed;

a first electrode formed on said metal contact layer;

a second electrode formed on said exposed second cladding layer;

a mirror formed beneath said LED epitaxial structure; and

an electroless copper substrate plated beneath said mirror and retaining sawing streets without plating the substrate thereon;

wherein said metal contact layer remains only the portion beneath the first electrode;

wherein the light emitting diode further comprising a film of Pd, coated beneath the metal layer of the mirror, to accelerate the reaction of electroless copper substrate.

Claim 35 (new): The light emitting diode as claimed in claim 34, wherein said electroless copper substrate is about 30μm thick.

Claim 36(new): The light emitting diode as claimed in claim 34, further comprising a transparent conductive film between said first electrode and said metal

contact layer.

Claim 37 (new): The light emitting diode as claimed in claim 34, wherein said metal contact layer remains only the portion beneath the first electrode.

Claim 38 (new): The light emitting diode as claimed in claim 34, wherein said mirror is made from a composite of a metal layer with low refractivity and an insulating layer with high refractivity selected from the group consisting of:

Al/MgF_2, Pt/Al_2O_3, Pt/SiO_2, Pt/MgF_2, Au/SiO_2, Au/MgF_2, Ag/MgF_2.

Claim 39 (new): The light emitting diode as claimed in claim 38, wherein said composite of a metal layer with low refractivity and an insulating layer with high refractivity is Au/SiO_2.